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(54) Title: BUTTED BODY CONTACT FOR SOI TRANSISTOR

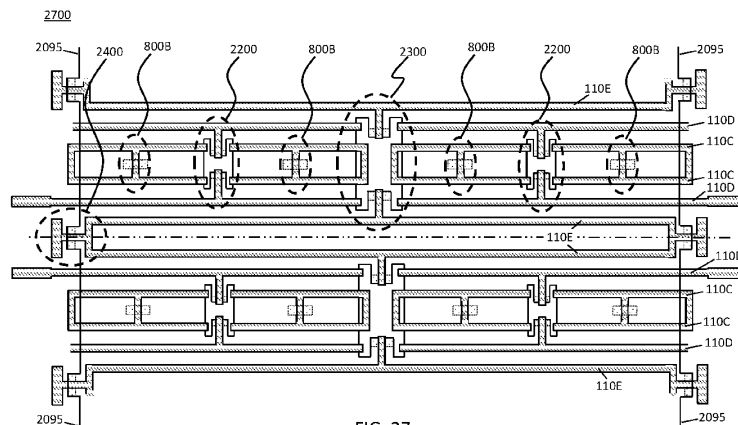


FIG. 27

(57) Abstract: Systems, methods, and apparatus for an improved body tie construction are described. The improved body tie construction is configured to have a lower resistance body tie exists when the transistor is "off" (V_g approximately 0 volts). When the transistor is "on" ($V_g > V_t$), the resistance to the body tie is much higher, reducing the loss of performance associated with presence of body tie. Space efficient Body tie constructions adapted for cascode configurations are also described.

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